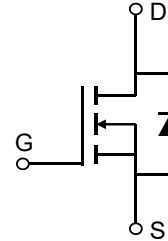


Description

Features

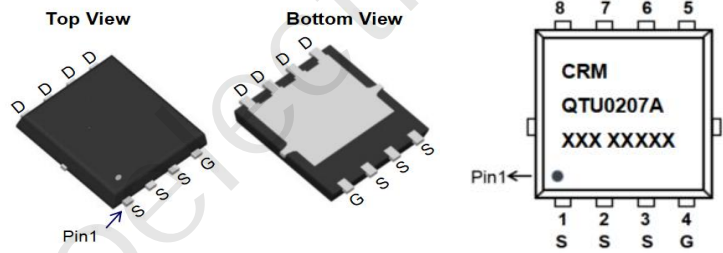
- 20V, 33A
- $R_{DS(ON)}$ Typ = 6.7mΩ @ $V_{GS} = 4.5V$
- $R_{DS(ON)}$ Typ = 9.0mΩ @ $V_{GS} = 2.5V$
- Advanced Trench Technology
- Excellent $R_{DS(ON)}$ and Low Gate Charge
- Lead Free
- 100% UIS TESTED!
- 100% ΔV_{ds} TESTED!



Schematic Diagram

Application

- Load Switch
- PWM Application
- Power Management



Marking and Pin Assignment

Package Marking and Ordering Information

Device	Marking	Package	Outline	Reel Size	Reel (pcs)	Per Carton (pcs)
CRMQTU0207A	CRMQTU0207A	PDFN3.3x3.3-8L	TAPING	13"	5000	50000

Absolute Maximum Ratings (@ $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Units
V_{DS}	Drain-to-Source Voltage	20	V
V_{GS}	Gate-to-Source Voltage	±12	V
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$	33
		$T_C = 100^\circ\text{C}$	19.8
I_{DM}	Pulsed Drain Current ⁽¹⁾	132	A
E_{AS}	Single Pulsed Avalanche Energy ⁽²⁾	20	mJ
P_D	Power Dissipation	$T_C = 25^\circ\text{C}$	17.8
$R_{\theta JC}$	Thermal Resistance, Junction to Case	7.5	$^\circ\text{C/W}$
T_J, T_{STG}	Junction & Storage Temperature Range	-55 to 150	$^\circ\text{C}$

Electrical Characteristics ($T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
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Off Characteristics

$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$I_D = 250\mu\text{A}, V_{GS} = 0\text{V}$	20	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 20\text{V}, V_{GS} = 0\text{V}$	-	-	1.0	μA
I_{GSS}	Gate-Body Leakage Current	$V_{DS} = 0\text{V}, V_{GS} = \pm 12\text{V}$	-	-	± 100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250\mu\text{A}$	0.5	0.7	1	V
$R_{DS(ON)}$	Static Drain-Source ON-Resistance ⁽³⁾	$V_{GS} = 4.5\text{V}, I_D = 15\text{A}$	-	6.7	8.7	mΩ
		$V_{GS} = 2.5\text{V}, I_D = 10\text{A}$	-	9	11.7	mΩ

Dynamic Characteristics

C_{iss}	Input Capacitance	$V_{GS} = 0\text{V}, V_{DS} = 10\text{V},$ $f = 1\text{MHz}$	-	1188	-	pF
C_{oss}	Output Capacitance		-	155	-	pF
C_{rss}	Reverse Transfer Capacitance		-	132	-	pF
Q_g	Total Gate Charge	$V_{GS} = 0 \text{ to } 4.5\text{V}$ $V_{DS} = 10\text{V}, I_D = 15\text{A}$	-	13	-	nC
Q_{gs}	Gate Source Charge		-	2.5	-	nC
Q_{gd}	Gate Drain("Miller") Charge		-	3.5	-	nC

Switching Characteristics

$t_{d(on)}$	Turn-On DelayTime	$V_{GS}=4.5\text{V}, V_{DD} = 10\text{V}$ $I_D = 15\text{A}, R_{GEN} = 3\Omega$	-	8	-	ns
t_r	Turn-On Rise Time		-	19	-	ns
$t_{d(off)}$	Turn-Off DelayTime		-	30	-	ns
t_f	Turn-Off Fall Time		-	11	-	ns

Drain-Source Diode Characteristics and Max Ratings

I_S	Maximum Continuous Drain to Source Diode Forward Current	$V_{GS} = 0\text{V}, I_S = 10\text{A}$	-	-	33	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	132	A
V_{SD}	Drain to Source Diode Forward Voltage		-	-	1.2	V
t_{rr}	Body Diode Reverse Recovery Time		-	7.5	-	ns
Q_{rr}	Body Diode Reverse Recovery Charge		-	1.5	-	nC

- Notes:
1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature.
 2. E_{AS} condition: Starting $T_J=25^\circ\text{C}$, $V_{DD}=10\text{V}$, $V_G=10\text{V}$, $R_G=25\text{ohm}$, $L=0.5\text{mH}$, $I_{AS}=9\text{A}$
 3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 0.5\%$.

Test Circuit



Figure 1: Gate Charge Test Circuit & Waveform



Figure 2: Resistive Switching Test Circuit & Waveform

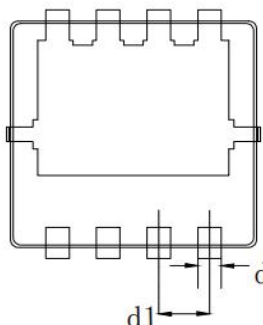
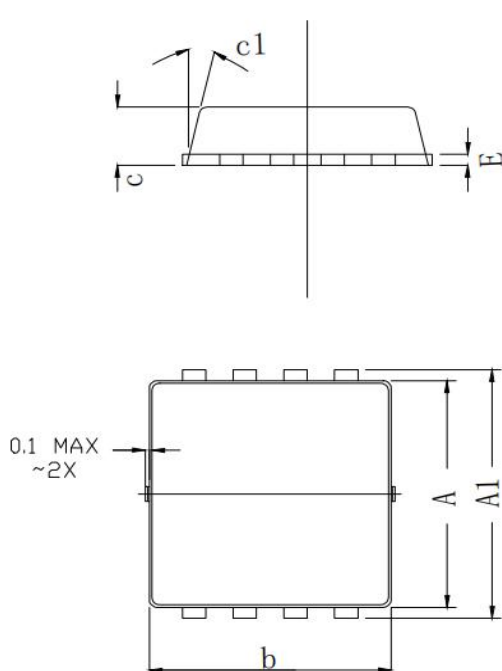


Figure 3: Unclamped Inductive Switching Test Circuit & Waveform



Figure 4: Diode Recovery Test Circuit & Waveform

Package Mechanical Data(PDFN3.3x3.3-8L)




COMMON DIMENSION (MM)			
PKG	PDFN 3.3×3.3-8L		
Symbol	MIN	MON	MAX
A	3.070	3.100	3.130
A1	3.300	3.400	3.500
b	3.070	3.100	3.130
c	0.770	0.800	0.830
c1	13°		
d	0.300		
d1	0.650		
E	0.152		

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